



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Group Art Unit: 2814
Examiner: Ngan V. Ngo

In re PATENT APPLICATION of

Applicant : Mu-Jen LAI et al.)

Appl. No. : 10/603,659 ✓)

Filed : June 26, 2003)

For : WHITE LIGHT LED)

Allowed : March 10, 2004)

Atty. Dkt. : SUND 466)

**INFORMATION
DISCLOSURE
STATEMENT**

Mail Stop ISSUE FEE

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:


This is an information disclosure statement submitted in compliance with the timing requirements of 37 C.F.R. §1.97(b)(3), i.e., prior to a first Office Action on the merits.

Attached are copies of two English-language articles, which are listed on the attached Form PTO-1449. Any relevance of the articles is self-evident. The articles were first cited by Taiwanese Patent Office on March 23, 2004.

Since this Information Disclosure Statement is being filed before a first Office Action, no certification or fee is required, and the requirements of 37 C.F.R. §§1.97 and 1.98 are deemed to be fully met as to all documents listed. Consideration of the listed documents respectfully is requested.

Respectfully submitted,

May 10, 2004
Date


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FORM PTO-1449 INFORMATION DISCLOSURE STATEMENT				Atty. Docket SUND 466		Application No. 10/603,659	
				Applicant Mu-Jen LAI et al.			
				Filing Date June 26, 2003		Group 2814	
U.S. PATENT DOCUMENTS							
Examiner Initial		Document Number	Date	Name	Class	Sub-Class	Filing Date
	AA						
	AB						
	AC						
	AD						
	AE						
	AF						
	AG						
	AH						
FOREIGN PATENT DOCUMENTS							
		Document Number	Date	Country	Class	Sub-Class	Translation
	AI						
	AJ						
	AK						
	AL						
OTHER (Including Author, Title, Date, Pertinent Pages, etc.)							
	AM	"ZnTe-GaN heterostructure switching device", A. G. Drizhuk et al.; Tech. Phys. Lett. 23 (10), October 1997; 1997 American Institute of Physics; pages 809 and 810					
	AN	"Growth of GaN on Si substrates – roles of BP thin layer" Optical Materials, S. Nishimura et al.; one page – ISI Web of Science 6.0					
Examiner					Date Considered		
EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.							